# Electron Transport through T-Shaped Double-Dots System

Yusuke Takazawa, Yoshiki Imai and Norio Kawakami

Department of Applied Physics, Osaka University, Suita, Osaka 565-0871

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Correlation e ects on electron transport through a system of T-shaped double-dots are investigated, for which only one of the dots is directly connected to the leads. We evaluate the local density of states and the conductance by means of the non-crossing approximation at nite temperatures as well as the slave-boson mean eld approximation at zero temperature. It is found that the dot which is not directly connected to the leads considerably in uences the conductance, making its behavior quite dierent from the case of a single-dot system. In particular, we not a novel phenomenon in the K ondo regime with a small inter-dot coupling, i.e. Fano-like suppression of the K ondo-mediated conductance, when two dot levels coincide with each other energetically.

KEYW ORDS: Kondo e ect, interference e ect, double dots

#### x1. Introduction

Recent intensive investigations of electron transport phenom ena through quantum dot systems have revealed that the strong electron-electron interaction plays a crucial role at low temperatures. In particular, the K ondo e ect, which is a prototypical many-body e ect, has been discovered in a single-dot system, stimulating further theoretical and experimental studies. 1,2,3,4,5,6,7,8,9,10) The K ondo e ect has been also observed in coupled quantum dots, 11,12,13,14) in which the inter-dot coupling is coulom bly controllable, making this system especially fascinating. In particular, from system atic studies on coupled quantum dots it has been pointed out that a wide variety of K ondo-like phenom ena can indeed o at low temperatures. 15,16,17,18,19,20)

There has been another remarkable phenomenon served in quantum dot systems, i.e. the Fanc fect,  $^{21,22,23,24)}$  which is caused by the interference tween two distinct resonant channels in the tunner process. When this elect is combined with the Ko elect, it may provide various interesting many-body fects by the interplay of both phenomena.

In this paper, we investigate tunneling phenom through a system of two coupled quantum dots in spe parallel-geom etry shown in Fig.1, which may be refe to as a system of T-shaped double dots. The syste also regarded as a single-dot system decollated by other dot, so that the additional right dot may ( a tunneling channel distinct from the direct resonvia the left dot, and is thus expected to give ris the interplay between the Kondo e ect and the Fa type interference e ect. By using non-crossing app im ation  $(NCA)^{25,26,27,28,29}$  approach for a general Anderson tunneling Hamiltonian, we calculate the : density of states (DOS) and the tunneling conducta The NCA approach is further supplem ented by the : tem perature calculation by means of slave-boson m eld (SBMF) approximation. 30,31) We discuss how

eral tunable param eters in uence the localDOS and the tunneling conductance. It is shown that the inter-dot coupling and the relative position of dot levels play an essential role for electron transport. In particular, we not that in the K ondo regime with a small inter-dot tunneling, the K ondo-mediated conductance is suppressed by the Fano-like interference e ect.

This paper is organized as follows. In the next section, we brie y describe the model and the method, and then in x3 we show the results obtained for the local DOS and the conductance. A brief sum mary is given in x4

## x2. M odeland M ethod

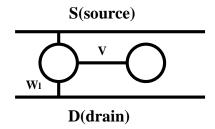


Fig. 1. T-shaped double-dots system in parallel geometry. The left dot is connected to both of the leads whereas the right dot is to the left one. The tunneling amplitude between the dots is V and that between the left dot and the leads is W  $_1$ .

### 2.1 Model Hamiltonian

We consider T-shaped double dots shown in Fig. 1. This system is described by an extended Anderson Hamiltonian for double dots,

$$H_{\text{med}} = \begin{matrix} X \\ & \\ & \end{matrix}_{k} \quad c_{k}^{y} \quad c_{k} \quad + \frac{1}{p-2} \begin{matrix} X \\ & \end{matrix}_{k} \quad (W_{1}c_{k}^{y} \quad d_{1} + h_{2}c_{k}^{y})$$

where  $d_i^y$  creates an electron in the left or right dot (labeled by i = 1;r) with the energy i and spin , whereas cy creates an electron in the leads specified by = s;d (source, drain) with the energy  $_k$  and spin  $\,$  .  $\,$  is the inter-dot tunneling am plitude while W  $_1$  is that between the left dot and the leads. We assume that the intradot Coulomb interaction is su ciently large to prohibit the double occupancy of electrons in each dot. To treat this situation, we apply the NCA to our model, which is known to give reasonable results in the temperature range larger than the Kondo temperature. 25,26,27) At lower temperatures the NCA may become inappropriate so that we adopt a complementary approach based on the SBM F approximation at zero temperature. 30,31)

# 2.2 NCA approach

Let us treat the Hamiltonian (1) by extending the NCA to the case possessing several kinds of ionic propagators. A similar extension of the NCA to the case of four ionic propagators has been applied successfully to the single impurity Anderson model with the nite Coulom b interaction. 28) In order to form ulate the G reen function for our double-dots model, we rst diagonalize the local Hamiltonian H loc, which can be expressed in term s of the H ubbard operators  $X_{m n} = j_m ihn jas$ 

$$H_{loc} = X^9$$
  $E_m X_{mm};$  (2)

where  $j_m$  i and  $E_m$  respectively denote the eigenstate of the local Hamiltonian and the corresponding eigenenergy. Recall that we should im pose the constraint on the Hilbert space such that double occupancy of electrons in each dot is forbidden. The remaining Hamiltonian H  $_{\rm m}$  ed can be also expressed in terms of the Hubbard operators

$$H_{m ed} = \begin{bmatrix} X & & & \\ & k & C_{k}^{y} & C_{k} \\ & & & \\ + & \frac{1}{P} \frac{X}{2} & X & \\ & & & W_{1}U_{nm}^{1} C_{k}^{y} & X_{nm} + h c); \end{cases} (3)$$

where the matrix element  $U_{nm}^{1}$  is given by

$$U_{nm}^{1} = \text{Im } \dot{\eta} \dot{q}_{1}^{y} \dot{\eta} \dot{\mathbf{n}} \dot{\mathbf{n}}$$

For each eigenstate in i, the ionic propagator and the corresponding local DOS are de ned by

$$P_{m} (!) = \frac{1}{! E_{m} m (!)};$$
 (5)

$$_{m}$$
 (!) =  $\frac{1}{2}$  Im  $P_{m}$  (! + i); (6)

and its self-energy is represented in term s of  $U_{nm}^{1}$  as

self-energy is represented in term 
$$s \circ f U_{nm}^{\perp}$$
 as
$$\begin{array}{ccc}
X \\
m & (!) = & (y_{mn}^{\perp} f + y_{nm}^{\perp} f) \\
& & Z_{1} \\
& & d f (_{mn} ) P_{n} (! + _{mn} ) & (_{nm}^{\perp} f)
\end{array}$$

where  $f() = [exp() + 1]^1$  is the Ferm i distribution function ( = 1=T), and we set  $_{m n}$  = if the number of particles accomm odated in jn i is larger (sm aller) than that in jni. We evaluate the self-energy m (!) in a self-consistent perturbation theory up to the second order in the hybridization W 1 as is usually done in the NCA. The left and right Green's functions are given

$$G_{1(r)}(!) = {X \atop mn} \mathcal{J}J_{mn}^{1(r)} \mathcal{J}hhX_{mn}; X_{nm} ii_!;$$
 (8)

$$Z_{loc} = X^9 Z$$
 $X_{loc} = A_m ():$  (10)

The localDOS for the i-th dot is thus expressed as

$$_{i}(!) = \frac{1}{-} \text{Im } G_{i}(! + i);$$
 (11)

and the conductance is 
$$G = \frac{2e^2}{h} X X^{\frac{Z}{1}} d! \frac{(f())}{e} _{1}(!); \quad (12)$$

is the tunneling strength, which is given by the source (drain) tunneling strength  $\,^{\rm s}$  (  $^{\rm d}$ ) via the relation =  $\frac{s d}{s+d}$ . We num erically iterate the procedure outlined above to obtain the conductance by extending the way of Y M eir et al<sup>32)</sup> for the single-dot system. In the following discussions, we assume that the hybridization between the left dot and the leads is given by s = d = 2 for simplicity.

Here, we make a brief comment on the vertex correction in our NCA form alism. It is known for the nite-U Anderson model that the vertex corrections in the local G reen function are not so important as far as the oneparticle spectral function is concerned. 28) It is expected that this is also the case for the present system, so that we neglect them in the following discussions.

### Slave-boson mean-eld approach

Since the NCA approach may not give reliable results at lower tem peratures, we perform complementary calculations of the conductance at zero tem perature by means of the SBMF theory. 30,31) We introduce a slave boson operator  $b_i^y$  and a ferm ion operator  $f_i^y$  , where  $b_i^y$  ( $f_i^y$ ) creates an empty state (a singly occupied state) in each dot under the constraint,

$$f_{i}^{y} f_{i} + b_{i}^{y} b_{i} = 1$$
: (13)

In thism ethod, the mixing term such as  $W_1c_k^y d_1$  in (1) is replaced by W  $_{1}c_{\nu}^{y}$   $f_{1}$   $b_{1}^{y}$ , etc. W e now apply a meaneld treatment to our model by replacing the boson operator by its mean value;  $b_i$ ;  $b_i^y$ !  $b_i$ . The Hamiltonian where we have introduced the Lagrange multipliers  $_{i}$ , the renormalized energy level in the i-th dot  $_{1}$  =  $_{i}$  +  $_{i}$  the renormalized tunneling V =  $V \, b_{l} b_{r}$ , and  $W_{1}$  =  $\frac{1}{2} \, W_{1} b_{1}$ . For the mean-eld Hamiltonian (14), we calculate the ground-state energy E  $_{qs}$  as

The mean-eld values of i and  $b_i$  can be determined self-consistently by minimizing  $E_{gs}$  with respect to i and  $b_i$ , or equivalently with respect to the renormalized parameters i, V and  $W_1$ . Then we can determine the conductance G by calculating the G reen's functions for both dots. The conductance is given by

$$G = \frac{2e^2}{h}^{X}$$
 T (! = 0); (16)

where T (! = 0) = 1(! = 0) is the transm ission probability.

This completes the formulation based on the NCA and the SBMF treatment. By calculating the local DOS in each dot from the above formulae, we can evaluate the tunneling conductance.

# x3. Numerical Results

We now discuss how transport properties of the T-shaped double-dots system are a ected by the interference of two dots. We show the results obtained by the NCA at nite temperatures together with the complementary SBMF results at zero temperature. We will use as the unit of the energy.

## 3.1 Tuning the inter-dot coupling

We rst discuss the results by changing the inter-dot coupling V system atically. The calculated conductance is plotted in Fig. 2 by choosing typical sets of the param eters corresponding roughly to (a) the K ondo regime and (b) the valence uctuation regime.

We start with the Kondo regime shown in Fig. 2(a). It is seen that the conductance is gradually enhanced with the decrease of the temperature almost in the whole range of V shown in the gure. For small V, the enhancement is clearly attributed to the Kondo e ect due to the left dot, which is indeed con med from the DOS shown in Fig. 3. Namely, for small inter-dot coupling (V = 0.1), it is seen that the left dot has the typical DOS expected for a single-dot Kondo system, while the right dot has a sharp delta-function type spectrum similarly to an isolated dot. When the inter-dot coupling becomes large, the left-and right-dot levels are mixed up considerably,

leading to the upper and lower levels given by

$$= \frac{1}{2}^{h} \binom{1}{1 + r}^{p} \frac{p}{(1 + r) + 4V^{2}}^{i} : (17)$$

The e ective upper level is pushed upward with the increase of V, resulting in the increase of the conductance. It should be noted that the conductance strongly depends on the tem perature even when the e ective upper level is located around the Ferm i level. Its temperature dependence is not due to the K ondo e ect, but is mainly caused by that of the Coulom b peak itself, as seen in the corresponding DOS for the intermediate inter-dot coupling V = 1:0 in Fig. 3. This implies that the electron correlations play a crucial role for the conductance even in this param eter regime. As the inter-dot tunneling further increases, the upper level goes beyond the Ferm ienergy. It is remarkable that a tiny resonance peak again appears around the Ferm i level. This peak is identied with the Kondo resonance because it gradually develops with the decrease of the tem perature, as seen in the inset of Fig. 3 (a). However, the resulting K ondo tem perature is rather sm all, and the conductance via the K ondo resonance is hindered by that caused by the upper level. Therefore in the parameter regime V 2:4, the conductance is not so much enhanced with the decrease of the tem perature, although the small K ondo peak indeed

As mentioned before, our NCA results become less reliable at low temperatures. To overcome this problem, we calculate the conductance by the SBMF theory at zero temperature. The results are shown in the inset of Fig. 2 (a). It is seen that for small V (0:1), the conductance is increased almost up to the unitary limit, while in the intermediate regime V 2, the conductance is not so much enhanced. In the strong V regime, the conductance is enhanced, but the elective K ondo peak is shifted slightly away from the Fermilevel, so it does not reach the unitary limit. In this way, the SBMF results con me that the conductance calculated by the NCA approach indeed gives reliable results.

We next discuss the valence—uctuation regime. The calculated conductance is shown in Fig. 2 (b), and the corresponding DOS is shown in Fig. 4. As mentioned above, when the inter-dot tunneling V increases, two dot levels are separated and thus the upper (lower) level is shifted beyond (below) the Ferm i level. Therefore, the conductance is decreased since the Coulomb peak disappears around the Ferm i level. This is indeed seen in the nite-tem perature NCA results as well as the zero-tem perature SBMF results in Fig. 2 (b). As mentioned in the case of the K ondo regime, in the large V regime, a tiny K ondo peak appears, which can be also seen in the DOS in Fig. 4.

# 3.2 Tuning the dot-levels

We now investigate how the conductance is changed when the energy level of the left or right dot is tuned. Thism ay be experimentally studied by changing the gate voltage.

### 3.2.1 Conductance control by the left dot

We start by exam ining the conductance as a function of the left-dot level, 1. The results are shown in Fig. 5. Most of the characteristic properties in this case can be understood from the discussions given in the previous subsection. In the weak inter-dot coupling regime shown in Fig. 5 (a), the conductance is enhanced due to the form ation of the K ondo resonance as the tem perature decreases when 1 is su ciently deep. As 1 approaches the Ferm i level, the conductance is dominated by the current via the bare resonance form ed around the e ective energy level of the left dot. This type of the interpretation is also valid for the strong inter-dot coupling regime shown in Fig. 5 (b), for which the e ective level should be replaced by the resultant upper level, + . In this case, the tem perature dependence of the conductance is understood by the sam e reason m entioned in Fig. 2 (b). We note that the K ondo peak appears again even for 1 0, but the conductance is mainly dominated by the resonance of the upper level existing near the K ondo peak.

### 3.2.2 Conductance control by the right dot

We nally discuss the conductance by tuning the energy level of the right dot,  $_{\rm r}$ . We again investigate two cases with small and large inter-dot coupling V. The results are summarized in Fig. 6. Let us start with the case of small V. When  $_{\rm r}$  of the right dot is deep below  $_{\rm l}$ , the conductance is mainly controlled by the Kondo mechanism of the left dot, as already mentioned before. This is also valid for the case when  $_{\rm r}$  is higher beyond  $_{\rm l}$ . These elects are indeed seen in the conductance of Fig. 6(a). Namely we can see the Kondo enhancement of conductance with the decrease of the temperature.

It should be remarked that we encounter a novel interference phenomenon, i.e. nontrivial suppression of the conductance, when two bare dot-levels coincide with each other. This is observed both in the NCA results as well as the SBMF results in Fig. 6 (a) around  $_{\rm r}$  2.0. This may be regarded as a Fano-like e ect caused by the interference between two distinct channels,  $^{21,22,23)}$  i.e. the direct K ondo resonance of the left dot and the indirect resonance via both of the right and left dots. As V becomes large, such interference is smeared, and cannot be observed in Fig. 6 (b). We wish to mention that this type of dip structure can be also seen in Fig. 5 (a) if the left level is varied through the point  $_{\rm l}$   $_{\rm r}$  = 3.0.

In order to clarify the origin of the interference e ect, we observe how the DOS changes its character when the right dot level is changed with V=0.1 being xed. It is seen in Fig.7 that when two localized levels are separated energetically, the DOS of the left dot is analogous to that for the ordinary single-dot Anderson model, which is slightly modiled around probability by the hybridization elect of the right dot. Therefore, in this parameter regime, the conductance is mainly controlled by the Kondo resonance of the left dot. However, when two levels are almost degenerate (r=1=2.0), the left and right states are equally mixed together to lift the degeneracy, and make two copies of similar DOS. As a consequence, this change around the bare levels indirectly modiles the

K ondo resonance, namely, it supresses the form ation of the K ondo peak around the Ferm i level, as seen from Fig.7 for  $_{\rm r}$  = 2.0. This thus gives rise to the decreace in the conductance. It is to be noted here that such an interference e ect occurs when the right level is changed in the energy range of the order of , while the relevant temperature range, in which such an e ect may be observable, is given by the elective K ondo temperature. Therefore, both of the bare and renormalized (K ondo) energy scales play a crucial role in this interference phenomenon.

It is instructive to point out that the interplay of the K ondo e ect and the interference e ect appears for sm aller V , which m ay be suitable for this e ect to be observed in experiments.

### x4. Sum m ary

We have studied electron transport in the T-shaped double-dots system as a function of the inter-dot coupling as well as the dot levels. We have calculated the tunneling conductance by exploiting the NCA at nite temperatures as well as the SBMF treatment at zero temperature. It has been found that though the electron current ows only through the left dot, its behavior is considerably a ected by the additional right dot via the interference electron. This demonstrates that the transport properties of the system may be controlled by properly tuning the parameters of the right dot which is indirectly connected to the leads.

In particular, we have found a rem arkable interference phenom enon for a sm all inter-dot coupling in the K ondo regim e; the conductance is suppressed when two bare dot-levels coincide with each other energetically, which is caused by the interference e ect between two distinct channels mediated by the left and right dots. This effect may be observed experimentally around or below the K ondo temperature by appropriately tuning the gate voltage for the dots in the range of the resonance energy due to the inter-dot coupling. In real double-dots systems, the inter-dot tunneling may be rather small, which may provide suitable conditions for our proposed phenomenon to be observed.

# A cknow ledgem ents

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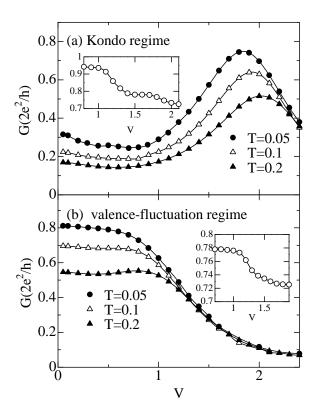


Fig. 2. Conductance for the T-shaped double-dots system as a function of the inter-dot coupling V at various temperatures: (a) K ondo regime with the bare energy levels  $_1=2.0$  and  $_r=3.0$ , (b) valence-uctuation regime with  $_1=1.0$  and  $_r=2.0$ . The inset shows the conductance computed by the SBMF approximation at zero temperature. In the K ondo regime (a), the electron number occupying the left (right) dot is  $n_1 = 1.0$ 0. ( $n_r = 1.0$ 1) for  $n_r = 1.0$ 1 for  $n_r = 1.0$ 2. On the other hand, in the valence uctuation regime (b),  $n_1 = 1.0$ 3.

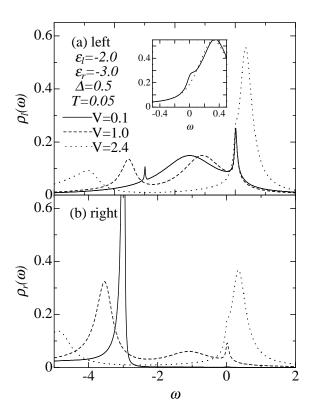


Fig. 3. Local density of states in the K ondo regime at T = 0:05: (a) left dot, (b) right dot. The solid, dashed and dotted lines correspond to the results for V = 0:1, V = 1:0 and V = 2:4 respectively. The inset in (a) shows  $_1(!)$  for V = 2:4, where the solid line is for T = 0:05 and the dotted line for T = 0:2. The e ective K ondo temperature is about 0.01 for V = 0. The Ferm i level is taken to be ! = 0.

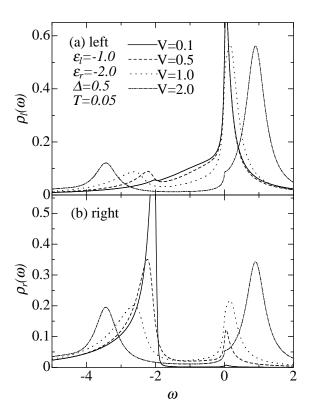
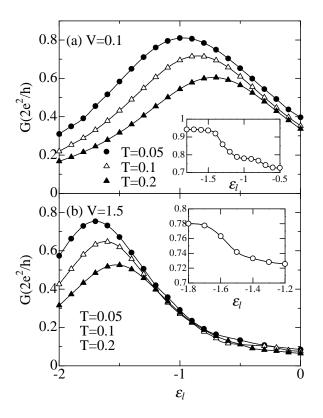


Fig. 4. Local density of states in the valence- uctuation regime at T=0.05: (a) left dot, (b) right dot. The solid, dashed, dotted and dot-dashed lines correspond to V=0.1, V=0.5, V=1.0 and V=2.0 respectively. The Ferm i level is taken to be !=0.



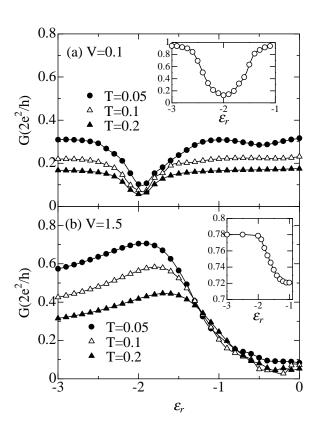


Fig. 5. Conductance for the T-shaped double-dots system as a function of the left-dot level  $_1\,w$  ith  $_r=~3:\!0$  being xed: (a) V = 0:1 and (b) V = 1:5.

Fig. 6. Conductance for the T-shaped double-dots system as a function of the right-dot level  $_{\rm r}$  with  $_{\rm l}$  =  $\,$  2:0 being xed: (a) V = 0:1 and (b) V = 1:5.

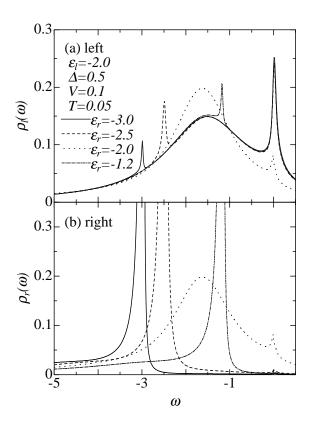


Fig. 7. Local density of states for V = 0:1. The energy level  $_{\rm r}$  of the right dot is system atically changed with a